Abstract

This invention is to provide a semiconductor laser device with a small interval between light emitting points of laser lights and a method of manufacturing the same. A first light emitting element 1a having a semiconductor substrate 12a and a laser oscillation section 10a, and a second light emitting element 2a having a laser oscillation section 4a, are brought together with a ridged waveguide 8 of the laser oscillation section 10a facing the ridged waveguide 5 of the laser oscillation section 4a, and then bonded together by virtue of SOGs 3a having a small thickness. A conductive wiring layer Qa1 electrically connected with an ohmic electrode layer 9a on the ridged waveguide 8a, and a wiring layer Qa2 electrically connected with an ohmic electrode layer 6a on the ridged waveguide 5a, are arranged to extend until the insulating layer 11a on the semiconductor substrate 12a. Further, the ohmic electrodes Pa1 and Pa2 are formed on the bottom surface of the semiconductor substrate 12a and the top surface of the laser oscillation section 4a, respectively. In this way, when a drive current is supplied between the ohmic electrode Pa1 and the wiring layer Qa1, the laser oscillation section 10a will emit a light. On the other hand, when a drive current is supplied between the ohmic electrode Pa2 and the wiring layer Qa2, the laser oscillation section 4a will emit a light. In this manner, since the laser oscillation sections 4a and 10a are bonded together by virtue of SOGs 3a having a small thickness, it is allowed to form a semiconductor laser device with a small interval between light emitting points.